

High throughput EUV Microscope TXM³ for single shot imaging

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A Transmission-type X-ray Multilayer Mirror Microscope (TXM³) for laboratory use has been developed using two pairs of normal-incidence reflection optics, one for illumination and the other for imaging, both coated with high throughput period-graded multilayers at a wavelength of 13.5 nm. The microscope is composed of the illumination-, sample- and detection- sections. In the illumination section, a point source of laser plasma, generated by a YAG laser (Spectra-Physics LAB-170) focused on a Sn evaporated glass rod is fed by a pair of illumination mirrors to the sample point at a NA of 0.24. A debris stopper was designed and mounted to stop all Sn particles flying at any speeds below 40m/sec. In the sample section, a sample is inserted by a three-axes goniometer of a side-entry type for easy operation. Between the sample and the illumination optics, a Zr membrane is installed to cut off visible light. In the detection section, a Schwarzschild objective (SO) of a 50X installation [1] was newly developed. The magnified image at 1m apart from the sample point is detected by a back illuminated CCD with 1024 × 1024 pixels, each of a 13 × 13 μm² area (Hamamatsu, C4742-98-24KAGD). For alignment of the SO and the sample position, a visible observation system was developed. All elements except for vacuum pumps are placed on a 1.8 × 1.5m² optical table of -30dB vibration isolation at 10Hz - 20Hz.

The Mo/Si multilayers for specific high-throughput imaging were prepared on super-polished mirror substrates by our ion-beam sputtering system, presented in an accompanying paper [2]. By the reflection band-pass matching among 4 mirrors, a total throughput of 0.1 was achieved. The wave-front error of the SO installed in a special housing with flexural hinges was 8 nm in RMS as measured by a Zygo interferometer. After alignments, the EUV image of a Cu#1500 mesh with Zr membrane roles was taken under EUV exposure by one laser shot of ≈10 nsec as shown in Fig. 1. The EUV intensity distribution is shown by a color scale conversion of the A/D converter output from the CCD. The spatial resolution estimated from the edge response was 440 nm in 20-80% band width. White regions in the figure give clear evidence that the EUV intensity of a single shot was above the saturation of the CCD camera.

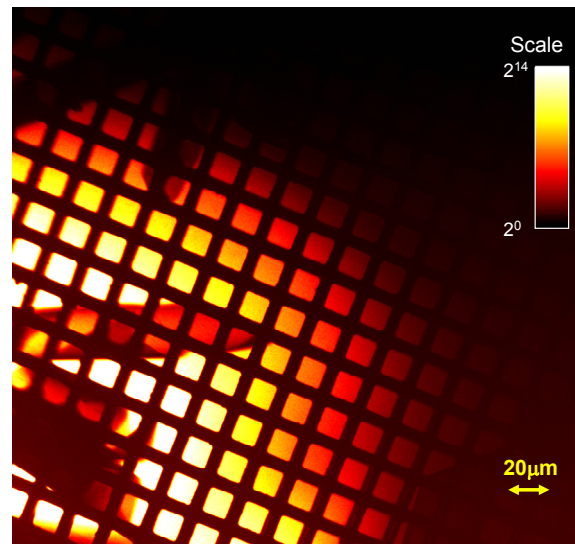


Figure 1: Single shot EUV image of Cu#1500 mesh with Zr membrane roles.

[1] M. Toyoda, et al., *Jpn. J. Appl. Phys.*, **39** (2000) 1926.

[2] T. Harada, T. Hatano, M. Yamamoto, "High Confidence Mo/Si Multilayer Deposition for the Transmission X-Ray Multilayer Mirror Microscope TXM³", **5.5**, 6/Feb/08 in this conference.